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Title: METHOD OF FORMING A GATE ELECTRODE, METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE HAVING THE GATE ELECTRODE, AND METHOD OF OXIDIZING A SUBSTRATE

INFORMATION DISCLOSURE CITATION
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U.S. PATENT DOCUMENTS

Exam Init	Ref	Document Number	Issue Date	Name	Class	Sub Class
_____	_____					

FOREIGN PATENT DOCUMENTS

Exam Init	Ref	Document Number	Publication Date	Country	Name
<u>Lu</u>	_____	JP8032066	2/2/1996	Japan	Katsuichi
<u>Lu</u>	_____	JP11345970	12/14/1999	Japan	Tomio et al.

OTHER DOCUMENTS

Exam Init	Ref	Author, Title, Date, Pertinent Pages, Etc.)
<u>Lu</u>	_____	English language of Abstract for Japanese Patent Publication No. JP8032066, filed 2/2/1996.
<u>Lu</u>	_____	English language of Abstract for Japanese Patent Publication No. JP11345970, filed 12/14/1999.

Examiner: Kevin Meng Lee

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